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Citation: Appl. Phys. Lett. 67, 1307 (1995); doi: 10.1063/1.114522
View online: http://dx.doi.org/10.1063/1.114522
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Flicker noise in YBa$_2$Cu$_3$O$_{7-\delta}$ bicrystal grain boundary junctions in weak magnetic fields

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(Received 10 April 1995; accepted for publication 5 July 1995)

Flicker noise in c-axis oriented long YBCO bicrystal grain boundary junctions was characterized as a function of temperature, biasing conditions, and magnetic field applied perpendicular to the $a$$-$$b$ plane over a wide range of temperatures from 15 K to over 70 K. Aperiodic variations, as a function of magnetic field, were observed in both the junction voltages, $V_J$, and the flicker noise magnitude under constant current bias as the magnetic field was scanned from 0 to 8 G. The noise magnitudes were found to peak at the minima of $V_J$. Analyses of the field dependencies of the magnitudes and the functional form of the voltage noise power spectra show that the noise did not arise from thermally activated flux motion. Based on the dependencies of the noise power spectra on the bias current and the dynamic resistance of the junction, we conclude that the noise originates from the fluctuations of the critical current of the devices most likely due to trapping of carriers or defect motion within the grain boundary. © 1995 American Institute of Physics.

Flicker noise in YBCO thin films and bicrystal junctions\textsuperscript{1$-$4} presents serious limitations in the low-frequency applications of high-$T_c$ superconducting quantum interference devices (SQUIDs). In this article we report experimental results on $1/f$ noise in YBCO bicrystal grain boundary junctions as a function of temperature, biasing conditions, and applied magnetic field.

High quality c-axis oriented YBCO thin films were deposited on SrTiO$_3$ bicrystal substrates by laser ablation. The $ab$-plane misorientation across the junction was 36.8\textdegree. Microbridges, ranging from 10 \textmu m to 50 \textmu m, were patterned using a standard photolithographic technique and EDTA etch. The critical temperature of the junctions at zero field was about 90.3 K with a transition region $<0.6$ K. Typical $I$--$V$ characteristics can be well fitted to the resistively shunted junction (RSJ) model with $J_C$ around $10^5$ A cm$^{-2}$ at $T=25.4$ K under zero field condition.

Field dependencies of the device characteristics were investigated with the magnetic field, $B_z$, applied perpendicular to the $a$$-$$b$ plane of the high-$T_c$ film. Strong aperiodic dependencies of the junction voltage, $V_J$, on $B_z$ were observed with the junction biased with a constant current and $B_z$ slowly varying from 0 to 8 G as shown in Fig. 1. This pattern can be viewed as a magneto-"fingerprint" (MF) of the junction disorder unique to each sample.\textsuperscript{5,6} Curves A and B represent $V_J$ measured for two different scans of the field separated by over an hour. A vertical shift is artificially introduced in the plots for comparison. In general, we found that the pattern remains unchanged as long as the devices were kept in low temperatures and small fields. Patterns and critical currents were strongly altered if fields $\geq$ 80 G were applied, most likely due to trapped flux.

Similar MF in the voltage noise power spectra across the junctions were also observed. The low-frequency noise was characterized with the device under constant current bias. Typical voltage noise power spectra, $S_V(f)$, varied as $1/f^\gamma$ where $\gamma=1.15$. Most interestingly, the noise power spectra were found to peak at the minima of $V_J$ as shown in Fig. 2. Here we show the detailed variations of $V_J$ (curve A) and $S_V$(100 Hz) (curve B) for $B_z$ between 5 and 6 G.

Recent studies of MF and noise in high-$T_c$ superconducting thin films suggested that the phenomenon originates from the simultaneous presence of flux flow and metastably pinned vortices.\textsuperscript{5} Aperiodic variations of critical current with field are expected for Josephson junctions with disorder, which leads to spatial fluctuations in the critical current density along the grain boundary. In long junctions the disorder can be viewed as a pinning potential for fluxons that pen-

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FIG. 1. Junction voltage vs $B_z$ at $I=2$ mA and $T=19.6$ K. Curves A and B represent two sets of data collected at times separated by at least 1 hr in between.
etrate the junction due to the presence of both the external field and applied currents. The pinning of a single fluxon within the junction area is still expected to set the dominant field scale for modulation of the voltage. The junction area is the length \(L = 40 \text{ mm}\) in the present case, times the magnetic thickness which is approximately twice the \(ab\) penetration depth, i.e., \(~0.5 \text{ mm}\), predicting a field scale of about \(1.0 \text{ G}\), quite consistent with the observations.

Although MF were observed in the \(1/f\) noise, this doesn’t imply that flux motion is ultimately responsible for the noise. Low-frequency noise arising from critical current fluctuations can occur due to carrier trapping, defect motion, or flux motion within or close to the junction. Our analysis show that the voltage noise power spectral density arising from critical current fluctuation noise can be expressed as

\[
S_v(f) = \frac{r^2(R_n^2 - V_J^2)}{f^2 R_n^2} S_{ic}(f) + \frac{r^2 V_J^2}{R_n^2 f^2 \frac{d V_J}{d B_z}} S_B(f),
\]

where \(r\) is the dynamic resistance, and \(R_n\) is the junction resistance in the RSJ model. The second term in Eq. (1) arises from field fluctuations due to flux motion in the vicinity of the junction. In Fig. 3 we plotted \(S_I\) versus \([V_J/(dV_J/dB_z)]^2\), in which \(S_I = S_V/r^2\). If the observed low-frequency noise originated from thermally activated flux motion, one would expect to see a slope of one in Fig. 3. Instead, we do not observe any dependencies between the two parameters. In addition, thermally activated fluxons producing critical current fluctuation noise would cause the spectrum to deviate noticeably from a power law \(^7\) and should result in large variations in \(\gamma\) as the pinning energy distribution varied with the applied field. \(^5\) This is in contrast to the voltage noise power spectra which always exhibit a power law and, while the noise increased by nearly two orders of magnitudes when \(B_z\) varied from 5.2 to 5.5 G, no detectable changes in \(\gamma\) were observed. Thus our experimental data strongly indicate that thermally activated flux motion is not responsible for the observed flicker noise in bicrystal grain boundary junctions, at least not well below \(T_C\).

Typical results on current dependencies of the \(1/f\) noise measured at \(B_z = 200 \text{ G}\) are shown in Fig. 4, where we have plotted the voltage noise power spectra for \(T = 34.7 \text{ K}\) and \(54.7 \text{ K}\), in which the solid and dashed lines are guides to the eye. The magnitudes of the voltage noise power spectra were found to increase with \(I\) initially but decrease at large \(I\), similar to Kawasaki’s \(^1\) observation for critical current fluctuations. In addition, the voltage noise power spectra exhibit, within experimental scatter, an \(r^2\) dependence as shown in Fig. 5. From Eq. (1), \(R_n\) is of the order of \(0.1 \Omega\) and is
relatively insensitive to the applied field, $I$ is kept constant at 2 mA, and $V_J$ typically varied between $10^{-5}$ and $10^{-6}$ V. Therefore $I^2R_n \gg V_J^2$ and $S_V(f) \propto r^2$ for flicker noise dominated critical current fluctuations. Thus our results are consistent with critical current fluctuations.

In conclusion, we have conducted detailed experimental studies of flicker noise in YBCO bicrystal grain boundary junctions in low magnetic fields. We observed magneto-fingerprints in both the junction voltage and the low-frequency noise due to the modulation with field of fluxon pinning within the junction. However, while flux motion affects the magnitude of the measured noise power spectra, it is not the underlying cause for flicker noise in the devices at low temperature. Our experimental results show that flicker noise in YBCO bicrystal junctions originates from critical current fluctuations most likely due to carrier trapping or motion of defects\(^8\) in the junction region.

The authors acknowledge the support of National Science Foundation Grant No. ECS-9102396.